Title;
21.5dBm Power-Handling 5GHz Transmit/Receive CMOS Switch
Realized by Voltage Division Effect of Stacked Transistor Configuration
with Depletion-Layer-Extended Transistors (DETs)

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[75 Word Abstract]
This paper reports for the first time an over-20dBm power-handling
5GHz transmit/receive (T/R) CMOS switch. The Depletion-layer-
Extended Transistor (DET) enables the voltage division effect of the
stacked transistor configuration to work in CMOS, thus realizing this high
power-handling capability. Furthermore, with the benefit of the
insertion-loss improvement effects in the DET, low insertion-losses of
0.95dB and 1.44dB are obtained at 5GHz in the transmit-mode and
receive-mode, respectively.